



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

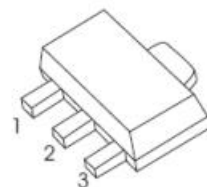
PXT3906

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

PNP Switching 开关

1. BASE
2. COLLECTOR
3. EMITTER



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-40	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-40	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-200	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

PXT3906=2A

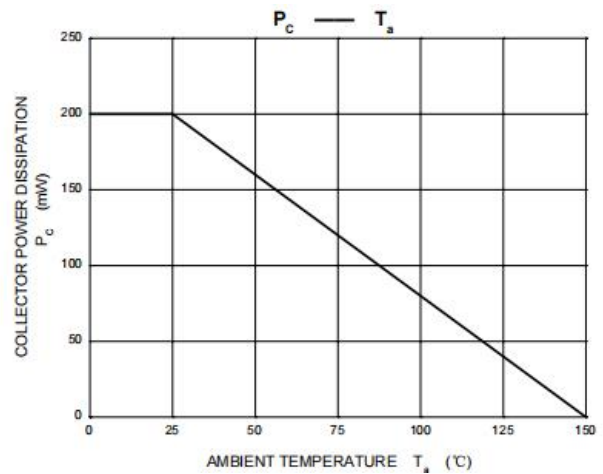
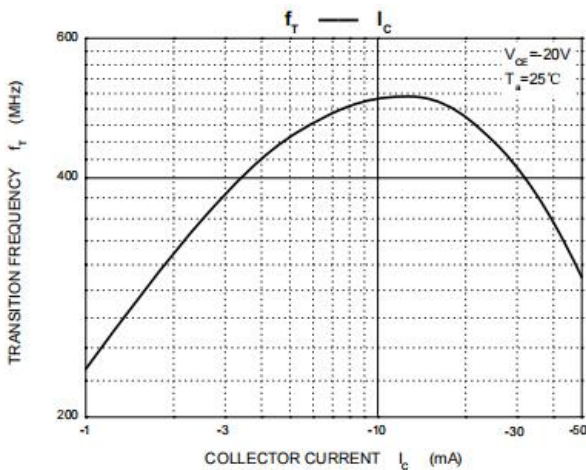
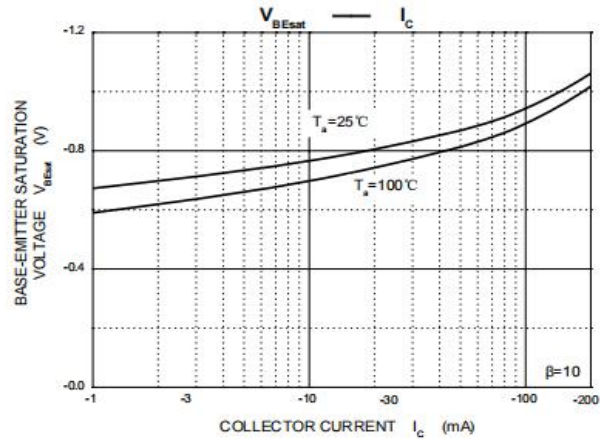
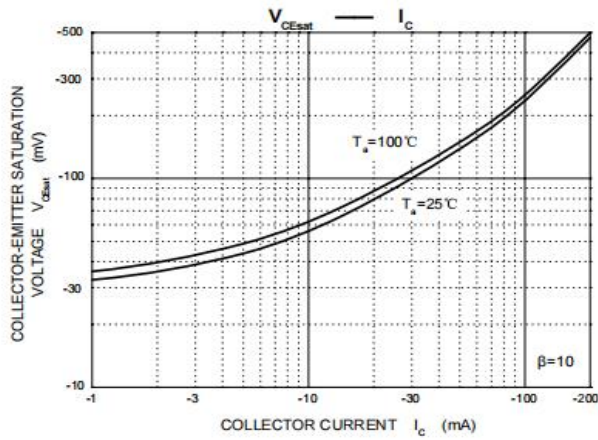
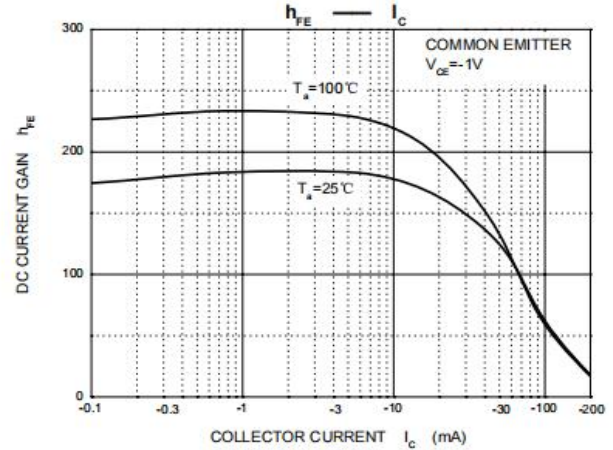
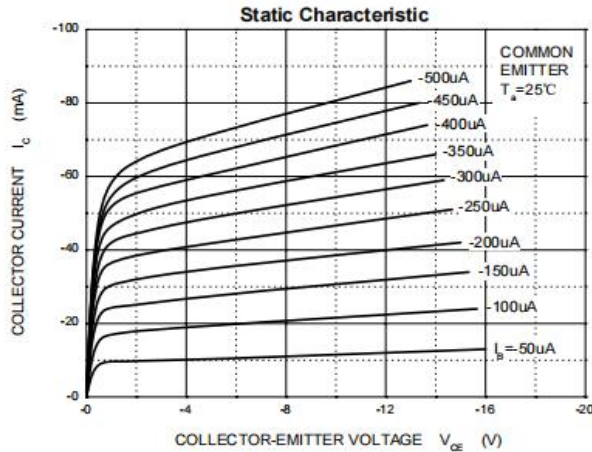


■ Electrical Characteristics 电特性

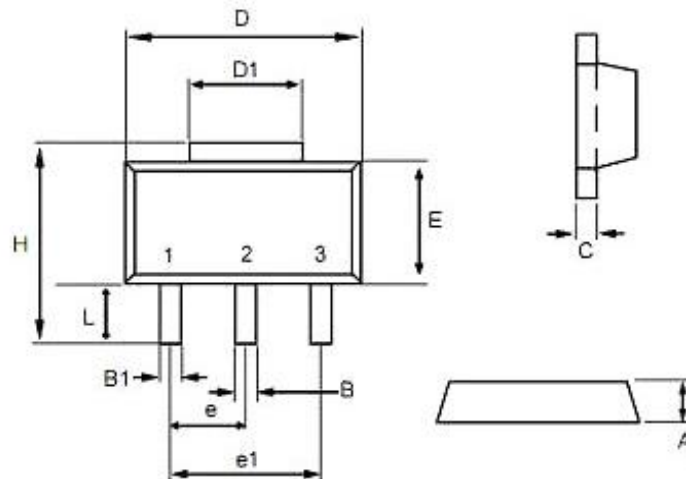
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C=-10\mu\text{A}$, $I_E=0$)	BV_{CBO}	-40	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C=-1\text{mA}$, $I_B=0$)	BV_{CEO}	-40	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E=-10\mu\text{A}$, $I_C=0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB}=-40\text{V}$, $I_E=0$)	I_{CBO}	—	—	-100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流($V_{CE}=-30\text{V}$, $V_{BE}=3\text{V}$)	I_{CEX}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB}=-5\text{V}$, $I_C=0$)	I_{EBO}	—	—	-100	nA
DC Current Gain($V_{CE}=-1\text{V}$, $I_C=-10\text{mA}$) 直流电流增益($V_{CE}=-1\text{V}$, $I_C=-50\text{mA}$) ($V_{CE}=-1\text{V}$, $I_C=-100\text{mA}$)	H_{FE}	100 60 30	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C=-50\text{mA}$, $I_B=-5\text{mA}$)	$V_{CE(sat)}$	—	—	-0.3	V
Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C=-50\text{mA}$, $I_B=-5\text{mA}$)	$V_{BE(sat)}$	—	—	-0.95	V
Transition Frequency 特征频率($V_{CE}=-20\text{V}$, $I_C=-10\text{mA}$)	f_T	300	—	—	MHz
Delay Time 延迟时间 ($V_{CC}=-3\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=-10\text{mA}$, $I_{B1}=-1\text{mA}$)	t_d	—	—	35	ns
Rise Time 上升时间 ($V_{CC}=-3\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=-10\text{mA}$, $I_{B1}=-1\text{mA}$)	t_r	—	—	35	ns
Storage Time 贮存时间 ($V_{CC}=-3\text{V}$, $I_C=-10\text{mA}$, $I_{B1}=I_{B2}=-1\text{mA}$)	t_s	—	—	225	ns
Fall Time 下降时间 ($V_{CC}=-3\text{V}$, $I_C=-10\text{mA}$, $I_{B1}=I_{B2}=-1\text{mA}$)	t_f	—	—	75	ns

Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20